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(54) **Title:** DISCRETE DUAL PADS FOR A CIRCUIT

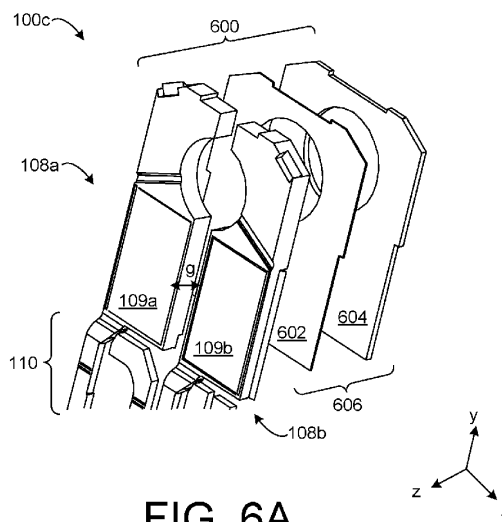


FIG. 6A

(57) **Abstract:** Implementations of high-power semiconductor device modules are described, including automotive power transistor assemblies for use in power amplifier circuits such as a cascode circuit (200). In some implementations, power amplifier circuit components are provided on separate semiconductor dies (104a, 104b) attached to discrete dual die attach pads (109a, 109b). A separation (g) between the die attach pads (109a, 109b), as well as a through-hole (412), provide sufficient isolation between the dies (104a, 104b) to permit operation of the circuit at high voltages without relying on a thick multi-layer direct bond copper (DBC) isolation structure. In some implementations, higher voltage operation can be supported by a thin multi-layer, resin coated copper DAP (600) in which the top layer is split.

[Continued on next page]

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